

GaAlAs-IR-Lumineszenzdiode (880 nm)
GaAlAs Infrared Emitter (880 nm)
Lead (Pb) Free Product - RoHS Compliant

SFH 486



Wesentliche Merkmale

- GaAlAs-LED mit sehr hohem Wirkungsgrad
- Hohe Zuverlässigkeit
- UL Version erhältlich
- Gute spektrale Anpassung an Si-Fotoempfänger
- Gegurtet lieferbar (im Ammo-Pack)
- Gruppiert lieferbar

Features

- Very highly efficient GaAlAs-LED
- High reliability
- UL version available
- Spectral match with silicon photodetectors
- Available on tape and reel (in Ammopack)
- Available in bins

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Rauchmelder
- Sensorik
- Diskrete Lichtschranken

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Smoke detectors
- Sensor technology
- Discrete interrupters

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 486	Q62703Q1094	5-mm-LED-Gehäuse (T 1 ³ / ₄), klares violettes Epoxy-Gießharz, Anschlüsse im 2.54-mm-Raster (1/10"), Anodenkennzeichnung: kürzerer Anschluß 5 mm LED package (T 1 ³ / ₄), violet-colored epoxy resin, solder tabs lead spacing 2.54 mm (1/10"), anode marking: short lead
SFH 486 E7517 (UL)	Q62703Q6175	

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlassstrom Forward current	I_F	100	mA
Stoßstrom, $t_p = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	2.5	A
Verlustleistung Power dissipation	P_{tot}	200	mW
Wärmewiderstand Thermal resistance	R_{thJA}	375	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$	λ_{peak}	880	nm
Spektrale Bandbreite bei 50% von I_{rel} Spectral bandwidth at 50% of I_{rel} $I_F = 100\text{ mA}$	$\Delta\lambda$	80	nm
Abstrahlwinkel Half angle	φ	± 11	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm ²
Abstand Chipoberfläche bis Gehäusevorderseite Distance chip front to case surface	H	5.1 ... 5.7	mm
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$	t_r, t_f	0.6/0.5	μs

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

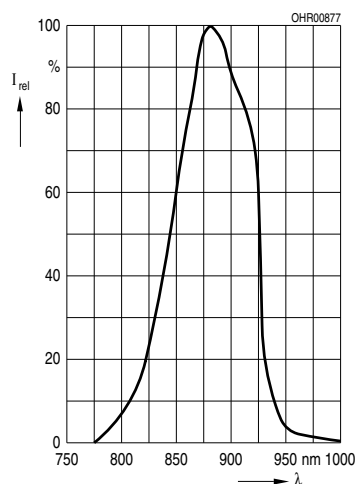
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Kapazität Capacitance $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_o	15	pF
Durchlassspannung Forward voltage $I_F = 100\text{ mA}, t_p = 20\text{ ms}$ $I_F = 1\text{ A}, t_p = 100\text{ }\mu\text{s}$	V_F	1.5 (< 1.8) 3.0 (< 3.8)	V
Sperrstrom Reverse current $V_R = 5\text{ V}$	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}, t_p = 20\text{ ms}$	Φ_e	25	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 2	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	0.25	nm/K

Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.001$ sr**Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.001$ sr

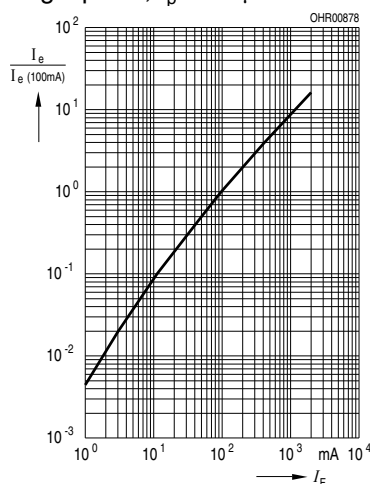
Bezeichnung Parameter	Symbol	Werte Values	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min}}$ $I_{e \text{ typ}}$	40 70	mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ}}$	600	mW/sr

Relative Spectral Emission

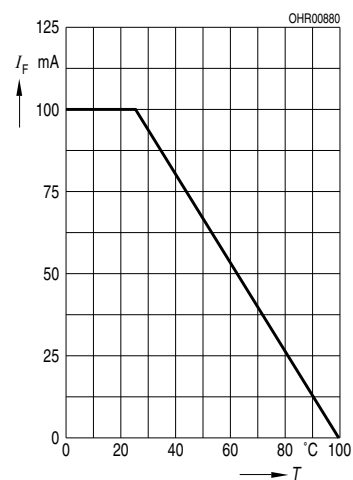
$I_{\text{rel}} = f(\lambda)$



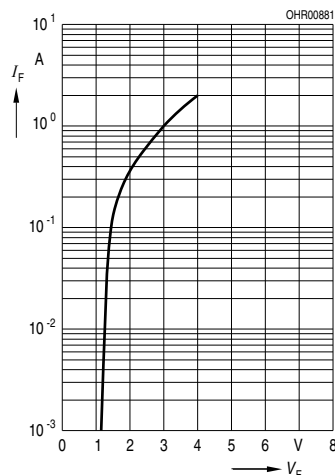
Radiant Intensity $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse, $t_p = 20 \mu\text{s}$ **Max. Permissible Forward Current**

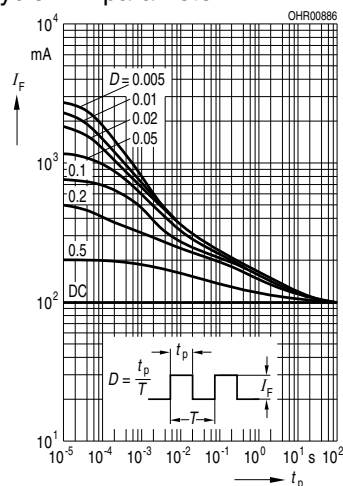
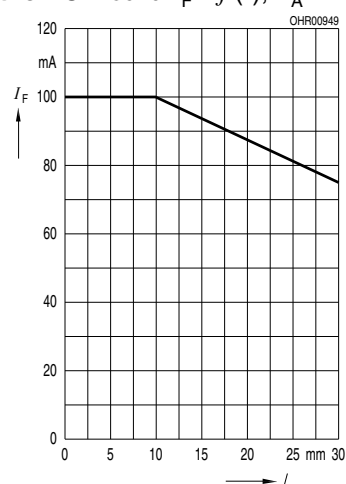
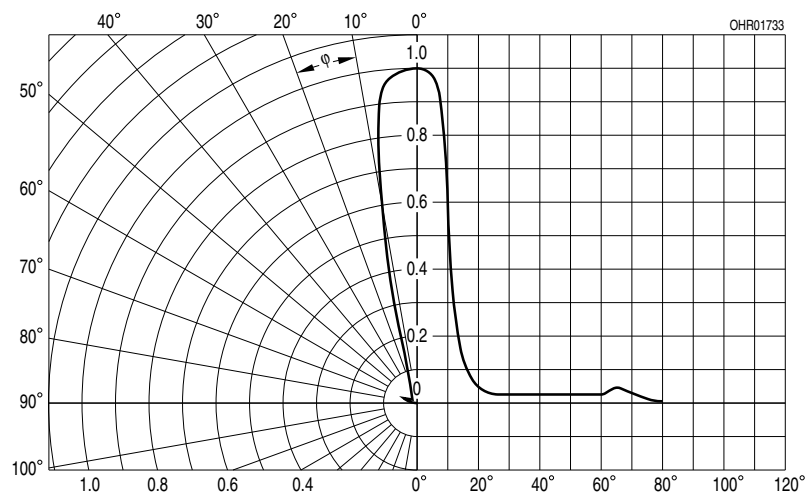
$I_F = f(T_A)$

**Forward Current**

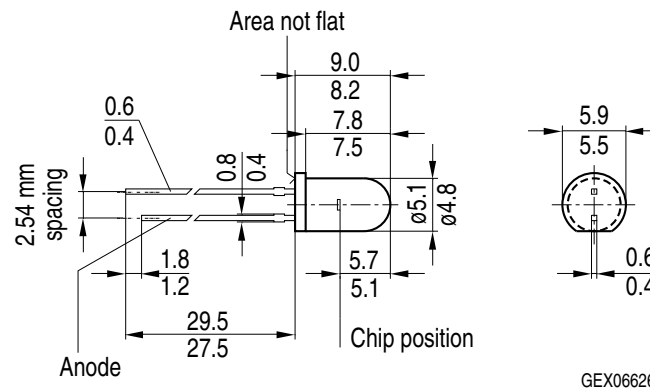
$I_F = f(V_F)$, single pulse, $t_p = 20 \mu\text{s}$

**Permissible Pulse Handling**

$I_F = f(\tau)$, $T_A = 25^\circ\text{C}$, duty cycle $D = \text{parameter}$

**Forward Current vs. Lead Length Between the Package Bottom and the PC-Board** $I_F = f(l)$, $T_A = 25^\circ\text{C}$ **Radiation Characteristics** $I_{\text{rel}} = f(\varphi)$ 

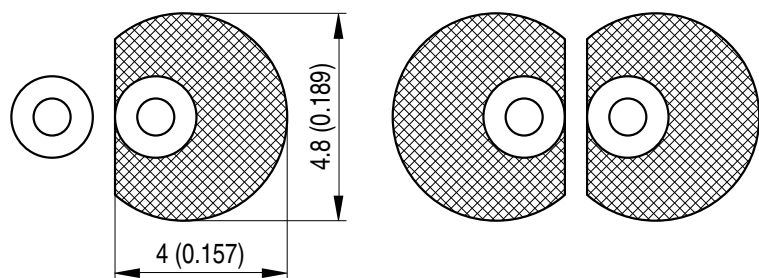
Maßzeichnung Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

Empfohlenes Lötpaddesign¹⁾ Recommended Solder Pad

Wellenlöten (TTW) TTW Soldering

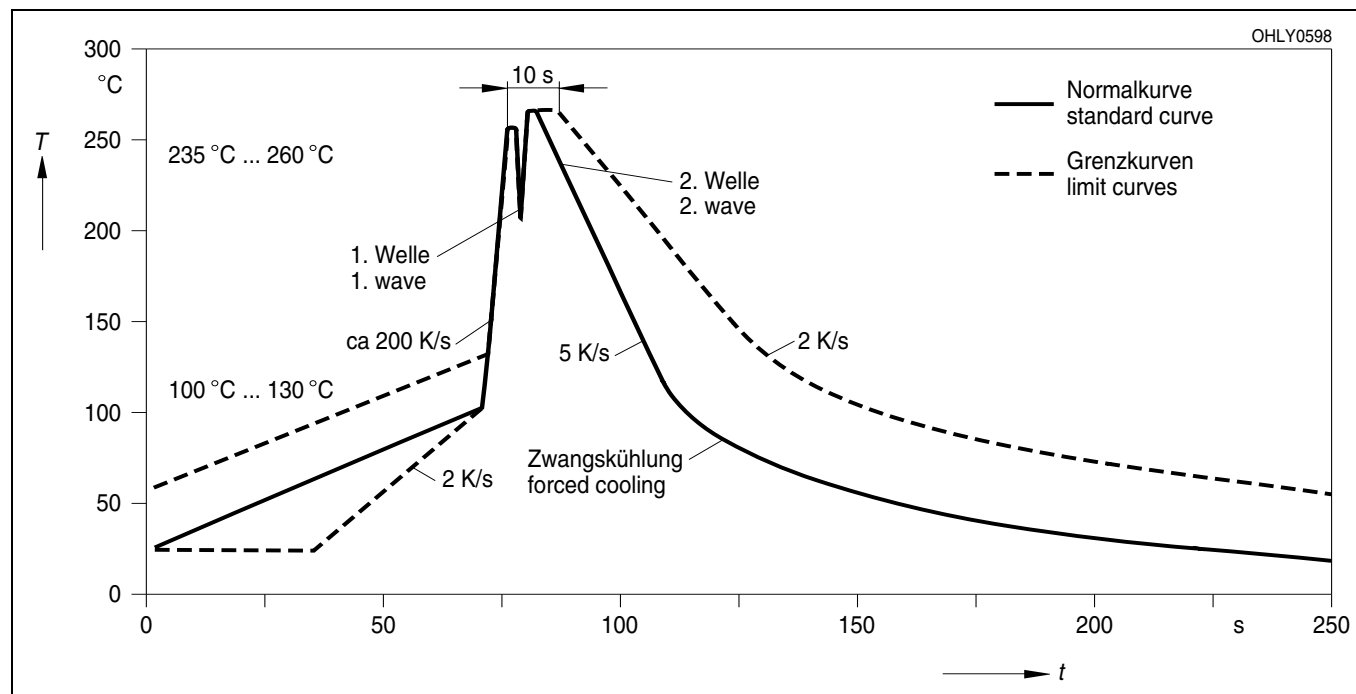


OHLPY985

Maße in mm (inch) / Dimensions in mm (inch).

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
 (acc. to CECC 00802)



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